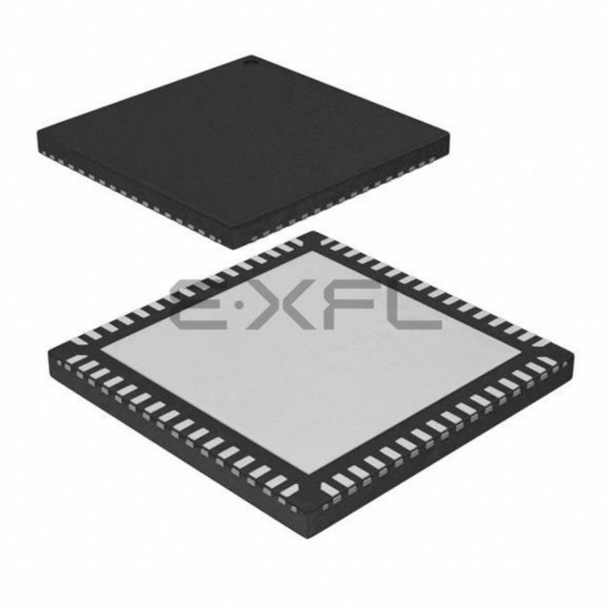
Silicon Labs - EFM32TG11B120F128GM64-A Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	56
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 12bit SAR; D/A 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg11b120f128gm64-a

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3.6.5 Controller Area Network (CAN)

The CAN peripheral provides support for communication at up to 1 Mbps over CAN protocol version 2.0 part A and B. It includes 32 message objects with independent identifier masks and retains message RAM in EM2. Automatic retransmittion may be disabled in order to support Time Triggered CAN applications.

3.6.6 Peripheral Reflex System (PRS)

The Peripheral Reflex System provides a communication network between different peripheral modules without software involvement. Peripheral modules producing Reflex signals are called producers. The PRS routes Reflex signals from producers to consumer peripherals which in turn perform actions in response. Edge triggers and other functionality such as simple logic operations (AND, OR, NOT) can be applied by the PRS to the signals. The PRS allows peripheral to act autonomously without waking the MCU core, saving power.

3.6.7 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface LESENSE^{TM} is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators, ADC, and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable finite state machine which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

3.7 Security Features

3.7.1 GPCRC (General Purpose Cyclic Redundancy Check)

The GPCRC module implements a Cyclic Redundancy Check (CRC) function. It supports both 32-bit and 16-bit polynomials. The supported 32-bit polynomial is 0x04C11DB7 (IEEE 802.3), while the 16-bit polynomial can be programmed to any value, depending on the needs of the application.

3.7.2 Crypto Accelerator (CRYPTO)

The Crypto Accelerator is a fast and energy-efficient autonomous hardware encryption and decryption accelerator. Tiny Gecko Series 1 devices support AES encryption and decryption with 128- or 256-bit keys, ECC over both GF(P) and GF(2^m), and SHA-1 and SHA-2 (SHA-224 and SHA-256).

Supported block cipher modes of operation for AES include: ECB, CTR, CBC, PCBC, CFB, OFB, GCM, CBC-MAC, GMAC and CCM.

Supported ECC NIST recommended curves include P-192, P-224, P-256, K-163, K-233, B-163 and B-233.

The CRYPTO module allows fast processing of GCM (AES), ECC and SHA with little CPU intervention. CRYPTO also provides trigger signals for DMA read and write operations.

3.7.3 True Random Number Generator (TRNG)

The TRNG module is a non-deterministic random number generator based on a full hardware solution. The TRNG is validated with NIST800-22 and AIS-31 test suites as well as being suitable for FIPS 140-2 certification (for the purposes of cryptographic key generation).

3.7.4 Security Management Unit (SMU)

The Security Management Unit (SMU) allows software to set up fine-grained security for peripheral access, which is not possible in the Memory Protection Unit (MPU). Peripherals may be secured by hardware on an individual basis, such that only priveleged accesses to the peripheral's register interface will be allowed. When an access fault occurs, the SMU reports the specific peripheral involved and can optionally generate an interrupt.

3.8 Analog

3.10 Core and Memory

3.10.1 Processor Core

The ARM Cortex-M processor includes a 32-bit RISC processor integrating the following features and tasks in the system:

- ARM Cortex-M0+ RISC processor
- Memory Protection Unit (MPU) supporting up to 8 memory segments
- Micro-Trace Buffer (MTB)
- Up to 128 kB flash program memory
- Up to 32 kB RAM data memory
- Configuration and event handling of all modules
- 2-pin Serial-Wire debug interface

3.10.2 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the microcontroller. The flash memory is readable and writable from both the Cortex-M and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block, whereas the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in energy modes EM0 Active and EM1 Sleep.

3.10.3 Linked Direct Memory Access Controller (LDMA)

The Linked Direct Memory Access (LDMA) controller allows the system to perform memory operations independently of software. This reduces both energy consumption and software workload. The LDMA allows operations to be linked together and staged, enabling sophisticated operations to be implemented.

3.10.4 Bootloader

All devices come pre-programmed with a UART bootloader. This bootloader resides in flash and can be erased if it is not needed. More information about the bootloader protocol and usage can be found in *AN0003: UART Bootloader*. Application notes can be found on the Silicon Labs website (www.silabs.com/32bit-appnotes) or within Simplicity Studio in the [**Documentation**] area.

4.1.8 Brown Out Detector (BOD)

Table 4.10. Brown Out Detector (BOD)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DVDD BOD threshold	$V_{DVDDBOD}$	DVDD rising	—	—	TBD	V
		DVDD falling (EM0/EM1)	TBD	—	—	V
		DVDD falling (EM2/EM3)	TBD	—	—	V
DVDD BOD hysteresis	$V_{DVDDBOD\_HYST}$		—	18	—	mV
DVDD BOD response time	$t_{DVDDBOD\_DELAY}$	Supply drops at 0.1V/μs rate	—	2.4	—	μs
AVDD BOD threshold	$V_{AVDDBOD}$	AVDD rising	—	—	TBD	V
		AVDD falling (EM0/EM1)	TBD	—	—	V
		AVDD falling (EM2/EM3)	TBD	—	—	V
AVDD BOD hysteresis	$V_{AVDDBOD\_HYST}$		—	20	—	mV
AVDD BOD response time	$t_{AVDDBOD\_DELAY}$	Supply drops at 0.1V/μs rate	—	2.4	—	μs
EM4 BOD threshold	$V_{EM4DBOD}$	AVDD rising	—	—	TBD	V
		AVDD falling	TBD	—	—	V
EM4 BOD hysteresis	V_{EM4BOD_HYST}		—	25	—	mV
EM4 BOD response time	t_{EM4BOD_DELAY}	Supply drops at 0.1V/μs rate	—	300	—	μs

4.1.9 Oscillators

4.1.9.1 Low-Frequency Crystal Oscillator (LFXO)

Table 4.11. Low-Frequency Crystal Oscillator (LFXO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal frequency	f_{LFXO}		—	32.768	—	kHz
Supported crystal equivalent series resistance (ESR)	ESR_{LFXO}		—	—	70	kΩ
Supported range of crystal load capacitance [1]	C_{LFXO_CL}		6	—	18	pF
On-chip tuning cap range [2]	C_{LFXO_T}	On each of LFXTAL_N and LFXTAL_P pins	8	—	40	pF
On-chip tuning cap step size	SS_{LFXO}		—	0.25	—	pF
Current consumption after startup [3]	I_{LFXO}	ESR = 70 kOhm, C_L = 7 pF, GAIN[4] = 2, AGC[4] = 1	—	273	—	nA
Start- up time	t_{LFXO}	ESR = 70 kOhm, C_L = 7 pF, GAIN[4] = 2	—	308	—	ms

Note:

1. Total load capacitance as seen by the crystal.
2. The effective load capacitance seen by the crystal will be C_{LFXO_T} /2. This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal.
3. Block is supplied by AVDD if ANASW = 0, or DVDD if ANASW=1 in EMU_PWRCTRL register.
4. In CMU_LFXOCTRL register.

4.1.10 Flash Memory Characteristics[5]

Table 4.17. Flash Memory Characteristics[5]

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Flash erase cycles before failure	EC_{FLASH}		10000	—	—	cycles
Flash data retention	RET_{FLASH}	T ≤ 85 °C	10	—	—	years
		T ≤ 125 °C	10	—	—	years
Word (32-bit) programming time	t_{W_PROG}	Burst write, 128 words, average time per word	20	26	32	µs
		Single word	59	68	83	µs
Page erase time[4]	t_{PERASE}		20	27	35	ms
Mass erase time[1]	t_{MERASE}		20	27	35	ms
Device erase time[2] [3]	t_{DERASE}	T ≤ 85 °C	—	54	70	ms
		T ≤ 125 °C	—	54	75	ms
Erase current[6]	I_{ERASE}	Page Erase	—	—	1.7	mA
		Mass or Device Erase	—	—	2.0	mA
Write current[6]	I_{WRITE}		—	—	3.5	mA
Supply voltage during flash erase and write	V_{FLASH}		1.62	—	3.6	V

Note:

1. Mass erase is issued by the CPU and erases all flash.
2. Device erase is issued over the AAP interface and erases all flash, SRAM, the Lock Bit (LB) page, and the User data page Lock Word (ULW).
3. From setting the DEVICEERASE bit in AAP_CMD to 1 until the ERASEBUSY bit in AAP_STATUS is cleared to 0. Internal setup and hold times for flash control signals are included.
4. From setting the ERASEPAGE bit in MSC_WRITECMD to 1 until the BUSY bit in MSC_STATUS is cleared to 0. Internal setup and hold times for flash control signals are included.
5. Flash data retention information is published in the Quarterly Quality and Reliability Report.
6. Measured at 25 °C.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
ADC clock frequency	f_{ADCCLK}		—	—	16	MHz
Throughput rate	$f_{ADCRATE}$		—	—	1	Msps
Conversion time[1]	$t_{ADCCONV}$	6 bit	—	7	—	cycles
		8 bit	—	9	—	cycles
		12 bit	—	13	—	cycles
Startup time of reference generator and ADC core	$t_{ADCSTART}$	WARMUPMODE[4] = NORMAL	—	—	5	μs
		WARMUPMODE[4] = KEEPIN-STANDBY	—	—	2	μs
		WARMUPMODE[4] = KEEPINSLO-WACC	—	—	1	μs
SNDR at 1Msps and f_{IN} = 10kHz	$SNDR_{ADC}$	Internal reference[7], differential measurement	TBD	67	—	dB
		External reference[6], differential measurement	—	68	—	dB
Spurious-free dynamic range (SFDR)	$SFDR_{ADC}$	1 MSamples/s, 10 kHz full-scale sine wave	—	75	—	dB
Differential non-linearity (DNL)	DNL_{ADC}	12 bit resolution, No missing codes	TBD	—	TBD	LSB
Integral non-linearity (INL), End point method	INL_{ADC}	12 bit resolution	TBD	—	TBD	LSB
Offset error	$V_{ADCOFFSETERR}$		TBD	0	TBD	LSB
Gain error in ADC	$V_{ADCGAIN}$	Using internal reference	—	-0.2	TBD	%
		Using external reference	—	-1	—	%
Temperature sensor slope	V_{TS_SLOPE}		—	-1.84	—	mV/°C

Note:

1. Derived from ADCCLK.
2. PSRR is referenced to AVDD when ANASW=0 and to DVDD when ANASW=1 in EMU_PWRCTRL.
3. In ADCn_BIASPROG register.
4. In ADCn_CNTL register.
5. The absolute voltage allowed at any ADC input is dictated by the power rail supplied to on-chip circuitry, and may be lower than the effective full scale voltage. All ADC inputs are limited to the ADC supply (AVDD or DVDD depending on EMU_PWRCTRL_ANASW). Any ADC input routed through the APORT will further be limited by the IOVDD supply to the pin.
6. External reference is 1.25 V applied externally to ADCnEXTREFP, with the selection CONF in the SINGLECTRL_REF or SCANCTRL_REF register field and VREFP in the SINGLECTRLX_VREFSEL or SCANCTRLX_VREFSEL field. The differential input range with this configuration is ± 1.25 V.
7. Internal reference option used corresponds to selection 2V5 in the SINGLECTRL_REF or SCANCTRL_REF register field. The differential input range with this configuration is ± 1.25 V. Typical value is characterized using full-scale sine wave input. Minimum value is production-tested using sine wave input at 1.5 dB lower than full scale.

4.1.14 Analog Comparator (ACMP)

Table 4.21. Analog Comparator (ACMP)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input voltage range	V_{ACMPIN}	ACMPVDD = ACMPn_CTRL_PWRSEL [1]	—	—	$V_{ACMPVDD}$	V
Supply voltage	$V_{ACMPVDD}$	BIASPROG[4] ≤ 0x10 or FULLBIAS[4] = 0	1.8	—	$V_{VREGVDD\_MAX}$	V
		0x10 < BIASPROG[4] ≤ 0x20 and FULLBIAS[4] = 1	2.1	—	$V_{VREGVDD\_MAX}$	V
Active current not including voltage reference[2]	I_{ACMP}	BIASPROG[4] = 1, FULLBIAS[4] = 0	—	50	—	nA
		BIASPROG[4] = 0x10, FULLBIAS[4] = 0	—	306	—	nA
		BIASPROG[4] = 0x02, FULLBIAS[4] = 1	—	6.5	—	μA
		BIASPROG[4] = 0x20, FULLBIAS[4] = 1	—	74	TBD	μA
Current consumption of internal voltage reference[2]	$I_{ACMPREF}$	VLP selected as input using 2.5 V Reference / 4 (0.625 V)	—	50	—	nA
		VLP selected as input using VDD	—	20	—	nA
		VBDIV selected as input using 1.25 V reference / 1	—	4.1	—	μA
		VADIV selected as input using VDD/1	—	2.4	—	μA

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Signal to noise and distortion ratio (1 kHz sine wave), Noise band limited to 250 kHz	$SNDR_{DAC}$	500 ksps, single-ended, internal 1.25V reference	—	60.4	—	dB
		500 ksps, single-ended, internal 2.5V reference	—	61.6	—	dB
		500 ksps, single-ended, 3.3V VDD reference	—	64.0	—	dB
		500 ksps, differential, internal 1.25V reference	—	63.3	—	dB
		500 ksps, differential, internal 2.5V reference	—	64.4	—	dB
		500 ksps, differential, 3.3V VDD reference	—	65.8	—	dB
Signal to noise and distortion ratio (1 kHz sine wave), Noise band limited to 22 kHz	$SNDR_{DAC\_BAND}$	500 ksps, single-ended, internal 1.25V reference	—	65.3	—	dB
		500 ksps, single-ended, internal 2.5V reference	—	66.7	—	dB
		500 ksps, differential, 3.3V VDD reference	—	68.5	—	dB
		500 ksps, differential, internal 1.25V reference	—	67.8	—	dB
		500 ksps, differential, internal 2.5V reference	—	69.0	—	dB
		500 ksps, single-ended, 3.3V VDD reference	—	70.0	—	dB
Total harmonic distortion	THD		—	70.2	—	dB
Differential non-linearity[3]	DNL_{DAC}		TBD	—	TBD	LSB
Intergral non-linearity	INL_{DAC}		TBD	—	TBD	LSB
Offset error[5]	V_{OFFSET}	T = 25 °C	TBD	—	TBD	mV
		Across operating temperature range	TBD	—	TBD	mV
Gain error[5]	V_{GAIN}	T = 25 °C, Low-noise internal reference (REFSEL = 1V25LN or 2V5LN)	TBD	—	TBD	%
		Across operating temperature range, Low-noise internal reference (REFSEL = 1V25LN or 2V5LN)	TBD	—	TBD	%
External load capactiance, OUTSCALE=0	C_{LOAD}		—	—	75	pF

4.1.16 Capacitive Sense (CSEN)

Table 4.23. Capacitive Sense (CSEN)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Single conversion time (1x accumulation)	t_{CNV}	12-bit SAR Conversions	—	20.2	—	µs
		16-bit SAR Conversions	—	26.4	—	µs
		Delta Modulation Conversion (single comparison)	—	1.55	—	µs
Maximum external capacitive load	C_{EXTMAX}	CS0CG=7 (Gain = 1x), including routing parasitics	—	68	—	pF
		CS0CG=0 (Gain = 10x), including routing parasitics	—	680	—	pF
Maximum external series impedance	R_{EXTMAX}		—	1	—	kΩ
Supply current, EM2 bonded conversions, WARMUPMODE=NORMAL, WARMUPCNT=0	I_{CSEN_BOND}	12-bit SAR conversions, 20 ms conversion rate, CS0CG=7 (Gain = 1x), 10 channels bonded (total capacitance of 330 pF)[1]	—	326	—	nA
		Delta Modulation conversions, 20 ms conversion rate, CS0CG=7 (Gain = 1x), 10 channels bonded (total capacitance of 330 pF)[1]	—	226	—	nA
		12-bit SAR conversions, 200 ms conversion rate, CS0CG=7 (Gain = 1x), 10 channels bonded (total capacitance of 330 pF)[1]	—	33	—	nA
		Delta Modulation conversions, 200 ms conversion rate, CS0CG=7 (Gain = 1x), 10 channels bonded (total capacitance of 330 pF)[1]	—	25	—	nA
Supply current, EM2 scan conversions, WARMUPMODE=NORMAL, WARMUPCNT=0	I_{CSEN_EM2}	12-bit SAR conversions, 20 ms scan rate, CS0CG=0 (Gain = 10x), 8 samples per scan[1]	—	690	—	nA
		Delta Modulation conversions, 20 ms scan rate, 8 comparisons per sample (DMCR = 1, DMR = 2), CS0CG=0 (Gain = 10x), 8 samples per scan[1]	—	515	—	nA
		12-bit SAR conversions, 200 ms scan rate, CS0CG=0 (Gain = 10x), 8 samples per scan[1]	—	79	—	nA
		Delta Modulation conversions, 200 ms scan rate, 8 comparisons per sample (DMCR = 1, DMR = 2), CS0CG=0 (Gain = 10x), 8 samples per scan[1]	—	57	—	nA

4.2.2 DC-DC Converter

Default test conditions: CCM mode, LDCDC = 4.7 µH, CDCDC = 4.7 µF, VDCDC_I = 3.3 V, VDCDC_O = 1.8 V, FDCDC_LN = 7 MHz

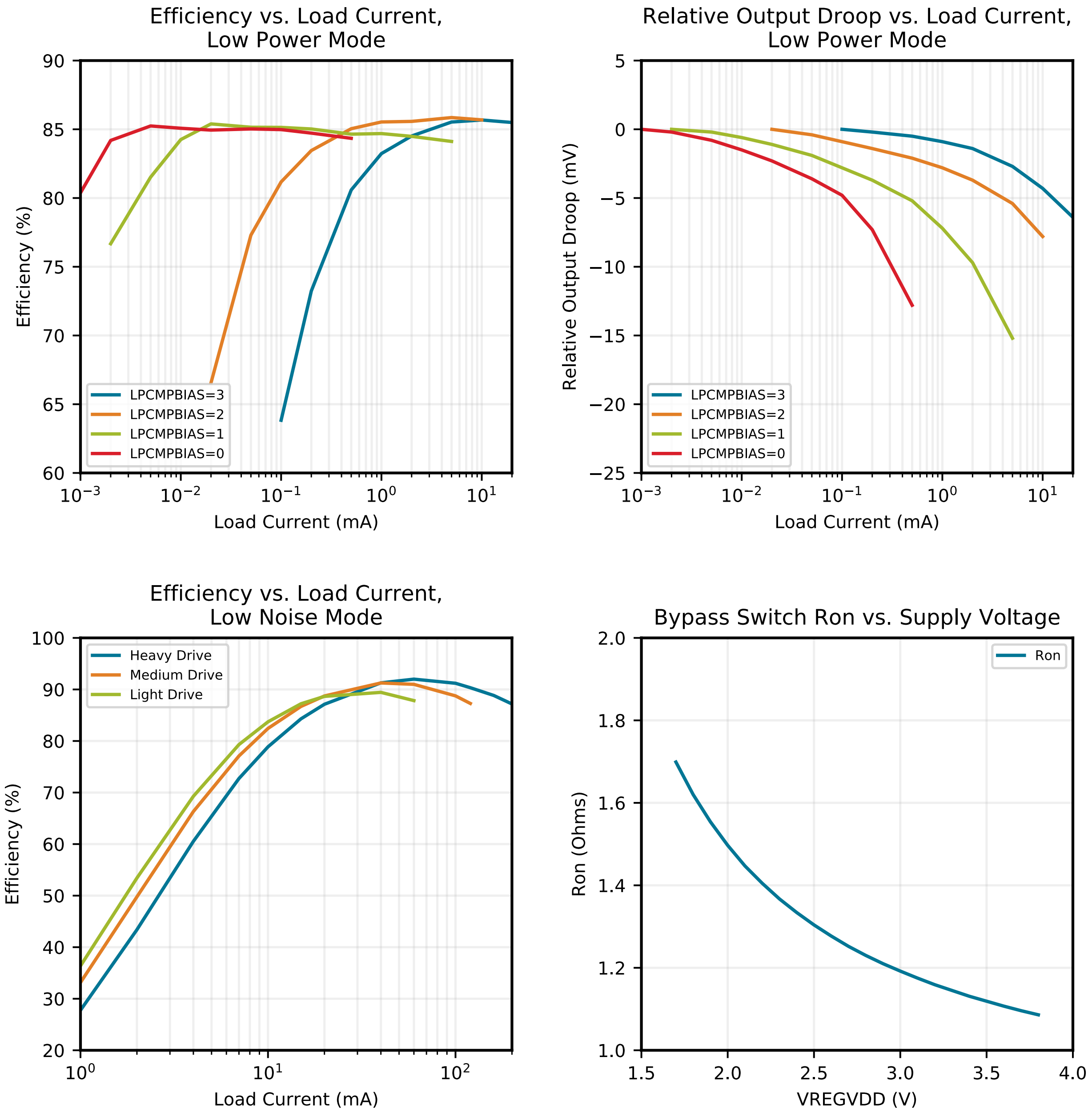

Figure 4.8. DC-DC Converter Typical Performance Characteristics

5. Pin Definitions

5.1 EFM32TG11B5xx in QFP80 Device Pinout

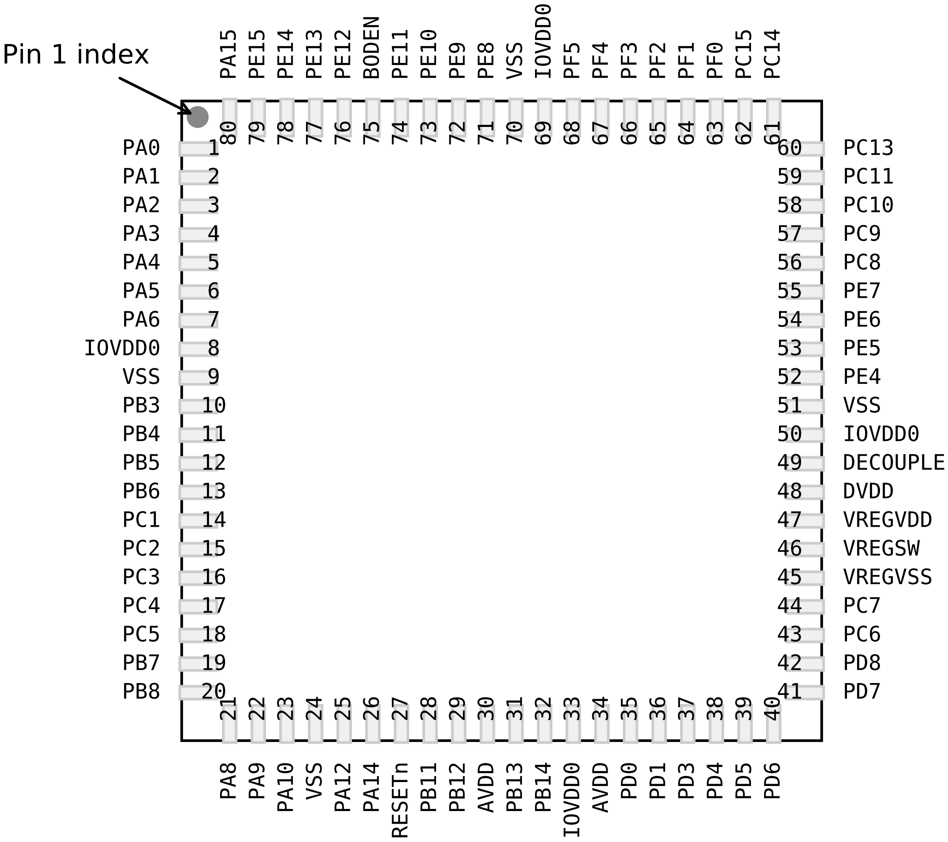

Figure 5.1. EFM32TG11B5xx in QFP80 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.14 GPIO Functionality Table or 5.15 Alternate Functionality Overview.

Table 5.1. EFM32TG11B5xx in QFP80 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
PA6	7	GPIO	IOVDD0	8 33 50 69	Digital IO power supply 0.

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE12	76	GPIO	PE13	77	GPIO
PE14	78	GPIO	PE15	79	GPIO
PA15	80	GPIO			

Note:

1. GPIO with 5V tolerance are indicated by (5V).

5.3 EFM32TG11B5xx in QFP64 Device Pinout

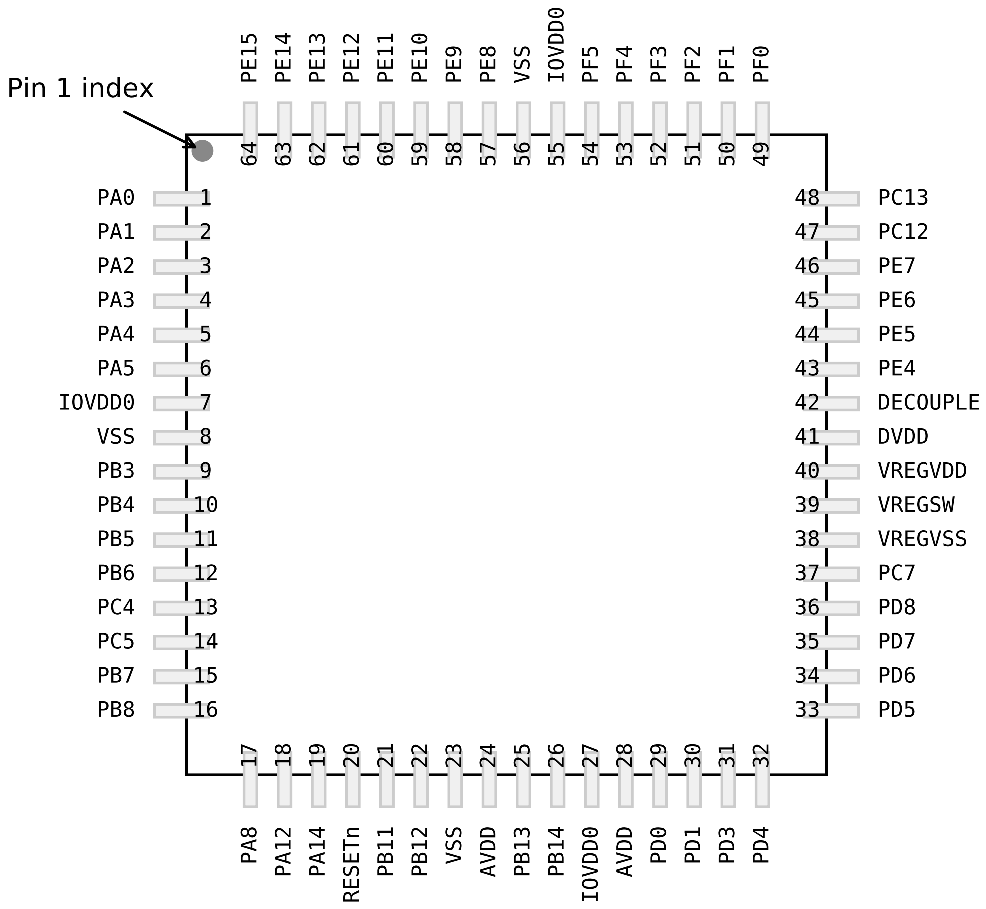

Figure 5.3. EFM32TG11B5xx in QFP64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.14 GPIO Functionality Table or 5.15 Alternate Functionality Overview.

Table 5.3. EFM32TG11B5xx in QFP64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
IOVDD0	7 27 55	Digital IO power supply 0.	VSS	8 23 56	Ground
PB3	9	GPIO	PB4	10	GPIO
PB5	11	GPIO	PB6	12	GPIO

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
LCD_SEG35	0: PC9		LCD segment line 35.
LES_ALTEX0	0: PD6		LESENSE alternate excite output 0.
LES_ALTEX1	0: PD7		LESENSE alternate excite output 1.
LES_ALTEX2	0: PA3		LESENSE alternate excite output 2.
LES_ALTEX3	0: PA4		LESENSE alternate excite output 3.
LES_ALTEX4	0: PA5		LESENSE alternate excite output 4.
LES_ALTEX5	0: PE11		LESENSE alternate excite output 5.
LES_ALTEX6	0: PE12		LESENSE alternate excite output 6.
LES_ALTEX7	0: PE13		LESENSE alternate excite output 7.
LES_CH0	0: PC0		LESENSE channel 0.
LES_CH1	0: PC1		LESENSE channel 1.
LES_CH2	0: PC2		LESENSE channel 2.
LES_CH3	0: PC3		LESENSE channel 3.

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
TIM0_CC0	0: PA0 2: PD1 3: PB6	4: PF0 5: PC4 6: PA8 7: PA1	Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	0: PA1 2: PD2 3: PC0	4: PF1 5: PC5 6: PA9 7: PA0	Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	0: PA2 2: PD3 3: PC1	4: PF2 6: PA10 7: PA13	Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI0	0: PA3 1: PC13 2: PF3 3: PC2	4: PB7	Timer 0 Complimentary Dead Time Insertion channel 0.
TIM0_CDTI1	0: PA4 1: PC14 2: PF4 3: PC3	4: PB8	Timer 0 Complimentary Dead Time Insertion channel 1.
TIM0_CDTI2	0: PA5 1: PC15 2: PF5 3: PC4	4: PB11	Timer 0 Complimentary Dead Time Insertion channel 2.
TIM1_CC0	0: PC13 1: PE10 3: PB7	4: PD6 5: PF2	Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	0: PC14 1: PE11 3: PB8	4: PD7 5: PF3	Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	0: PC15 1: PE12 3: PB11	4: PC13 5: PF4	Timer 1 Capture Compare input / output channel 2.
TIM1_CC3	0: PC12 1: PE13 2: PB3 3: PB12	4: PC14 6: PF5	Timer 1 Capture Compare input / output channel 3.
U0_CTS	2: PA5 3: PC13	4: PB7 5: PD5	UART0 Clear To Send hardware flow control input.
U0_RTS	2: PA6 3: PC12	4: PB8 5: PD6	UART0 Request To Send hardware flow control output.
U0_RX	2: PA4 3: PC15	4: PC5 5: PF2 6: PE4	UART0 Receive input.

Alternate	LOCATION		
Functionality	**0 - 3**	**4 - 7**	**Description**
VDAC0_OUT0 / OPA0_OUT	0: PB11		Digital to Analog Converter DAC0 output channel number 0.
VDAC0_OUT0ALT / OPA0_OUTALT	0: PC0 1: PC1 2: PC2 3: PC3	4: PD0	Digital to Analog Converter DAC0 alternative output for channel 0.
VDAC0_OUT1 / OPA1_OUT	0: PB12		Digital to Analog Converter DAC0 output channel number 1.
VDAC0_OUT1ALT / OPA1_OUTALT	0: PC12 1: PC13 2: PC14 3: PC15	4: PD1	Digital to Analog Converter DAC0 alternative output for channel 1.
WTIM0_CC0	0: PE4 1: PA6	4: PC15 6: PB3 7: PC1	Wide timer 0 Capture Compare input / output channel 0.
WTIM0_CC1	0: PE5	4: PF0 6: PB4 7: PC2	Wide timer 0 Capture Compare input / output channel 1.
WTIM0_CC2	0: PE6	4: PF1 6: PB5 7: PC3	Wide timer 0 Capture Compare input / output channel 2.
WTIM0_CDTI0	0: PE10 2: PA12	4: PD4	Wide timer 0 Complimentary Dead Time Insertion channel 0.
WTIM0_CDTI1	0: PE11 2: PA13	4: PD5	Wide timer 0 Complimentary Dead Time Insertion channel 1.
WTIM0_CDTI2	0: PE12 2: PA14	4: PD6	Wide timer 0 Complimentary Dead Time Insertion channel 2.
WTIM1_CC0	0: PB13 1: PD2 2: PD6 3: PC7	5: PE7	Wide timer 1 Capture Compare input / output channel 0.
WTIM1_CC1	0: PB14 1: PD3 2: PD7	4: PE4	Wide timer 1 Capture Compare input / output channel 1.
WTIM1_CC2	0: PD0 1: PD4 2: PD8	4: PE5	Wide timer 1 Capture Compare input / output channel 2.

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
WTIM1_CC3	0: PD1 1: PD5 2: PC6	4: PE6	Wide timer 1 Capture Compare input / output channel 3.

6. TQFP80 Package Specifications

6.1 TQFP80 Package Dimensions

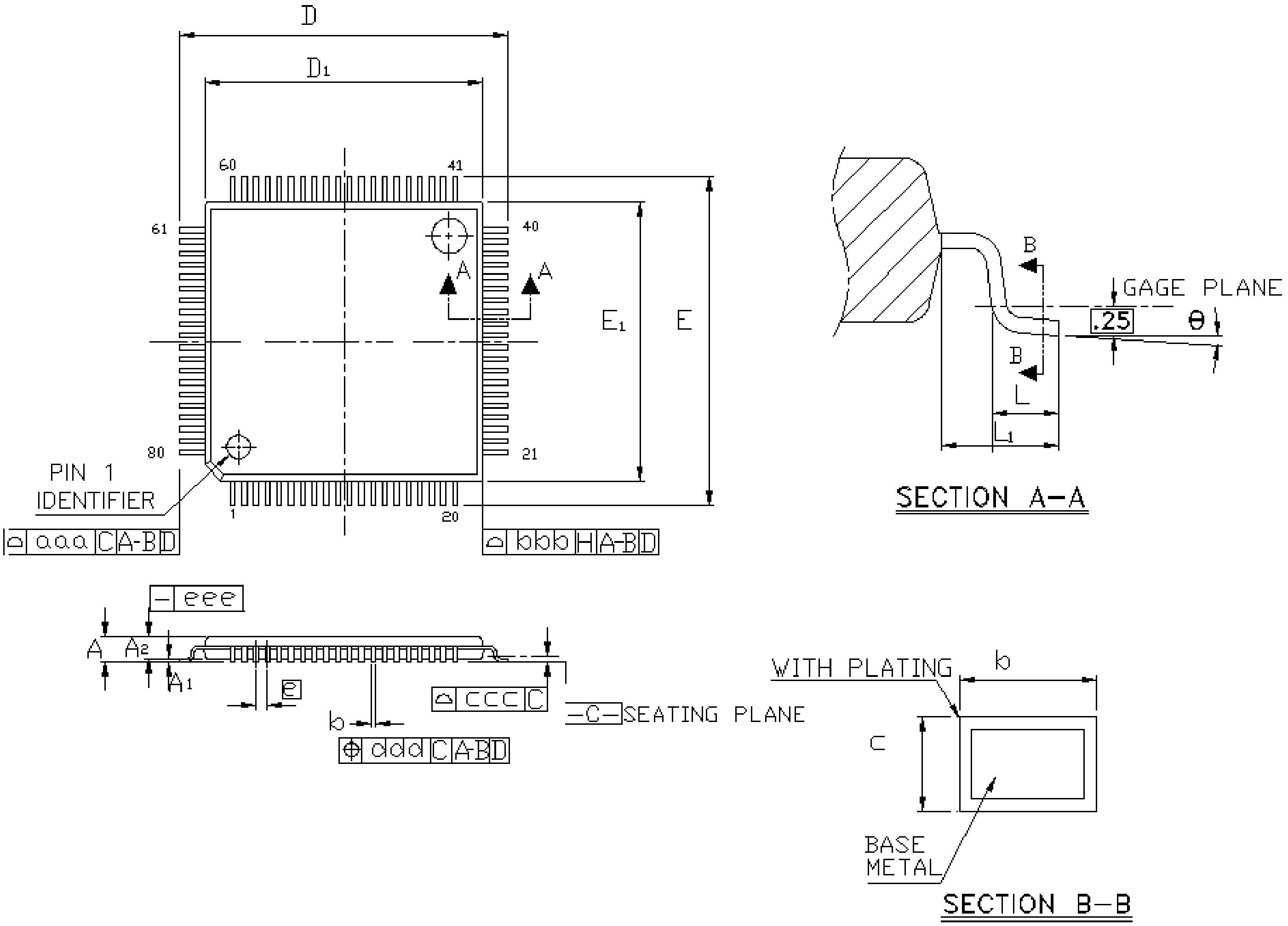

Figure 6.1. TQFP80 Package Drawing

8.2 TQFP64 PCB Land Pattern

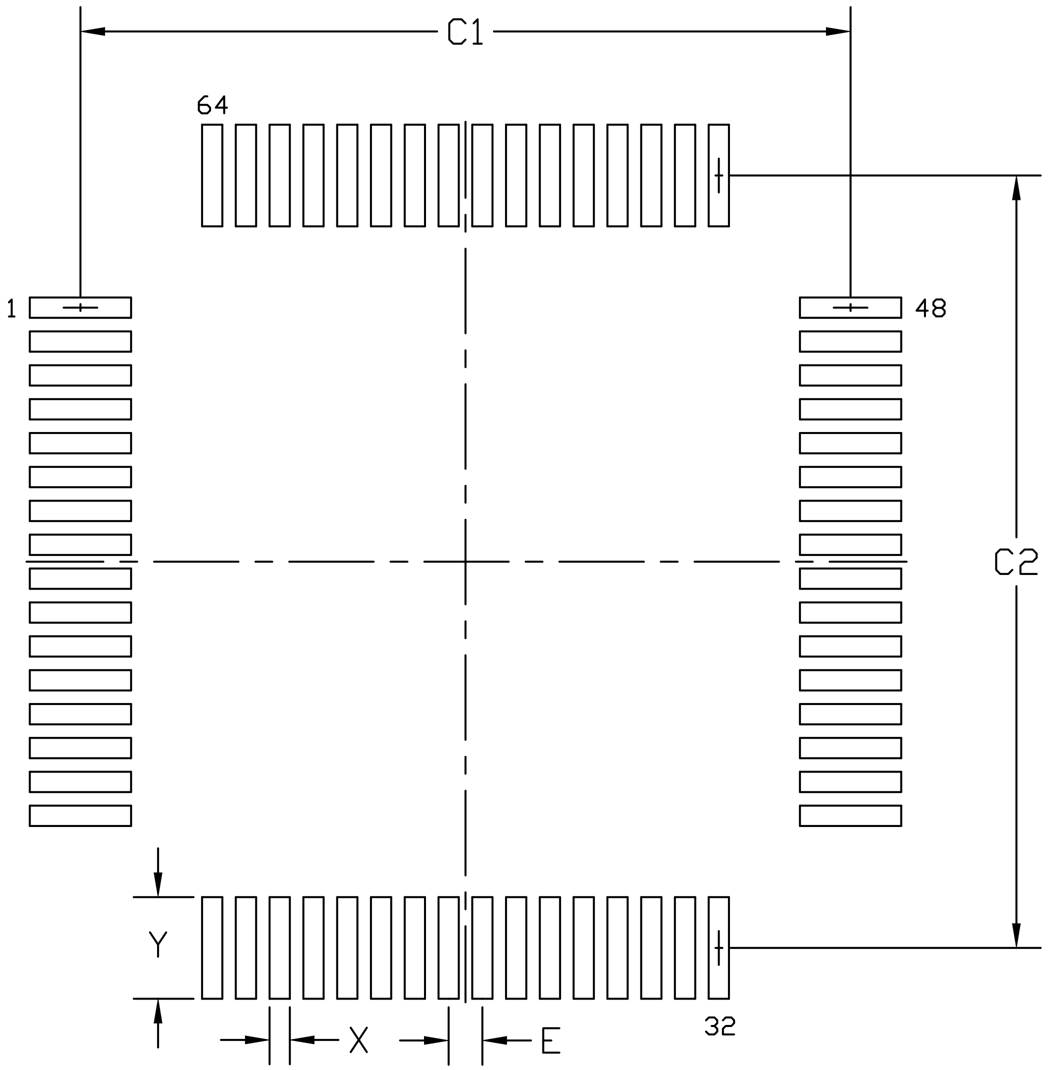

Figure 8.2. TQFP64 PCB Land Pattern Drawing